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SUPPLEMENTAL DECLARATION

As a below-named inventor, I hereby declare that:

My residence, post office address, and citizenship are as stated below next to my name,

I believe I am the original, first and sole inventor (if only one name is listed below) or an original, first and joint inventor (if plural names are listed below) of the subject matter which is claimed and for which a patent is sought on the invention entitled "High Electron Mobility Transistor and Method of Manufacture", the specification of which

was filed on May 9, 1991 as  
Application Serial No. 697,830  
and was amended on January 7, 1991  
(if applicable)

I hereby state that I have reviewed and understand the contents of the above-identified specification, including the claims, as amended by any amendment referred to above.

I acknowledge the duty to disclose information which is material to the examination of this application in accordance with Title 37, Code of Federal Regulations, §1.56(a).

I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under §1001 of Title 18 of the United States Code and that such willful false statements may jeopardize the validity of the application or any patent issued thereon.

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Full name of first inventor: John C. Huang

Inventor's signature

Residence: Cambridge, MA 02138

Citizenship: United States of America

Post Office Address: 44 Concord Avenue, Cambridge, MA 02138

Date April 9, 1992

Raytheon Case No. 35441

ALNS-5A

8/23/90

Full name of second inventor: Gordon S. Jackson

Inventor's signature Gordon S. Jackson

Residence: Belmont, MA 02178

Citizenship: United States of America

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Date 13 April 1992

Raytheon Case No. 35441

ALNS-5A

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